CLAIM AMENDMENTS:

Claim 1 (Canceled).

Claim 2 (Currently amended): The combined semiconductor apparatus according to claim 5, wherein said planarized region is a part of said surface of said ~~semiconductor~~ silicon substrate which has been subjected to a planarizing process.

Claims 3 and 4 (Canceled).

Claim 5 (currently amended): A combined semiconductor apparatus, comprising:

a ~~semiconductor~~ silicon substrate having an integrated circuit formed therein, the silicon substrate having a rough or irregular surface due to at least a wiring pattern of the integrated circuit;

a planarized region defined over said rough or irregular surface of said silicon substrate;

a planarized film disposed over said planarized region; and

a semiconductor thin film disposed over said planarized film, the semiconductor thin film including ~~at least one semiconductor device~~ a light-emitting element and being bonded on [[a]] said planarized film, so that said semiconductor thin film is disposed above the integrated circuit and said

planarized film electrically connects said light-emitting element to said integrated circuit ~~region defined on a surface of said semiconductor substrate~~, wherein:

said semiconductor thin film is made of a compound semiconductor as a main material; and

~~a planarized film disposed between said planarized region and said semiconductor thin film, wherein~~ a surface of said planarized film on a side of said semiconductor thin film has been subjected to a planarizing process.

Claim 6 (Currently amended): The combined semiconductor apparatus according to claim 5, wherein said planarized film includes:

an electrically conductive layer contacting with said light-emitting element; and

an interdielectric layer formed in a region peripheral to said electrically conductive layer.

Claims 7 and 8 (Canceled).

Claim 9 (Currently amended): The combined semiconductor apparatus according to claim 5, wherein said semiconductor thin film has a common electrode layer on a second surface of the semiconductor thin film opposed to a first surface of the semiconductor thin film, in which said ~~semiconductor device~~ light-emitting element is formed, and

said second surface of said semiconductor thin film is disposed on a side of said planarized region of said ~~semiconductor~~ silicon substrate.

Claim 10 (Currently amended): The combined semiconductor apparatus according to claim 9, wherein said integrated circuit includes individual electrode terminals; and

said apparatus further comprising individual interconnecting lines formed on a region extending from an upper surface of said ~~semiconductor device~~ light-emitting element to said individual electrode terminal.

Claims 11- 17 (Canceled).

Claim 18 (Currently amended): The combined semiconductor apparatus according to claim 5, wherein said ~~at least one semiconductor device~~ light-emitting element is a plurality of said ~~semiconductor devices~~ light-emitting elements arranged in said semiconductor thin film.

Claim 19 (Canceled).

Claim 20 (previously presented): An optical print head including the combined semiconductor apparatus of claim 5.

Claims 21-36 (Canceled).